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| 1. | 795 | | USPAT | 2004/05/24 16:57 |
| 2 | 485 | 438/681 | USPAT | 2004/05/24 16:57 |
| 3 | 962 | 438/683 | USPAT | 2004/05/24 16:57 |
| 4 | 288 | 438/684 | USPAT | |
| 5 | 998 | 438/680 | | 2004/05/24 16:58 |
| 6 - | 777 | 438/649 | USPAT | 2004/05/24 16:58 |
| 7 | 259 | 438/650 | USPAT | 2004/05/24 16:58 |
| 8 | 259 | 438/651 | USPAT | 2004/05/24 16:58 |
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| 1.1 | 460 | 438/657 | USPAT | 2004/05/24 16:58 |
| 12 | 370 | 438/668 | USPAT | 2004/05/24 16:58 |
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| 18 | 151 | 438/954 | USPAT | 2004/05/24 16:59 |
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| 22 | 1779 | 438/301 | USPAT | 2004/05/24 16:59 |
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| 24 | 406 | 438/304 | USPAT | 2004/05/24 16:59 |
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